

# PSMN4R0-25YLC

N-channel 25 V 4.5 mΩ logic level MOSFET in LPAK

Rev. 01 — 2 December 2010

Product data sheet

## 1. Product profile

### 1.1 General description

Logic level enhancement mode N-channel MOSFET in LPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising Superjunction technology
- Ultra low QG, QGD & QOSS for high system efficiencies at low and high loads

### 1.3 Applications

- DC-to-DC converters
- Load switching
- Power OR-ing
- Server power supplies
- Sync rectifier

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$	-	-	25	V
$I_D$	drain current	$V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 1</a>	-	-	84	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 2</a>	-	-	61	W
$T_j$	junction temperature		-55	-	175	°C

#### Static characteristics

$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}$ ; $I_D = 20\text{ A}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 12</a>	-	4.5	5.8	mΩ
		$V_{GS} = 10\text{ V}$ ; $I_D = 20\text{ A}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 12</a>	-	3.5	4.5	mΩ

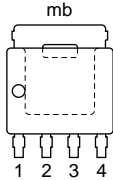
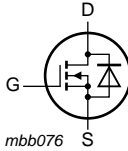


**Table 1. Quick reference data ...continued**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$V_{GS} = 4.5\text{ V}; I_D = 20\text{ A};$ $V_{DS} = 12\text{ V};$ see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	3.5	-	nC
$Q_{G(tot)}$	total gate charge	$V_{GS} = 4.5\text{ V}; I_D = 20\text{ A};$ $V_{DS} = 12\text{ V};$ see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	10.9	-	nC

## 2. Pinning information

**Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p>SOT669 (LPAK)</p>	 <p>mbb076</p>
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

## 3. Ordering information

**Table 3. Ordering information**

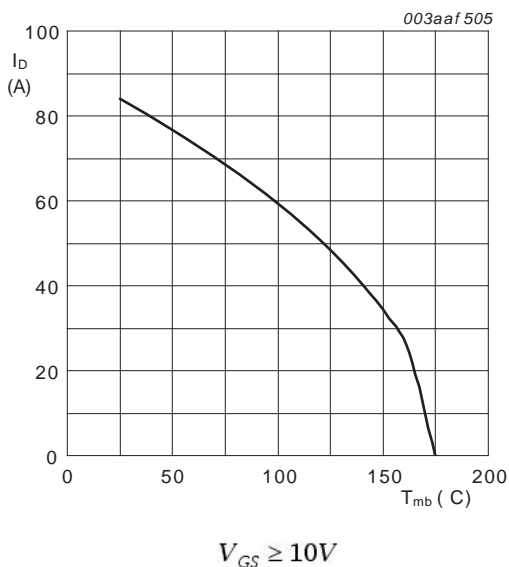
Type number	Package		Version
	Name	Description	
PSMN4R0-25YLC	LPAK	plastic single-ended surface-mounted package (LPAK); 4 leads	SOT669

### 4. Limiting values

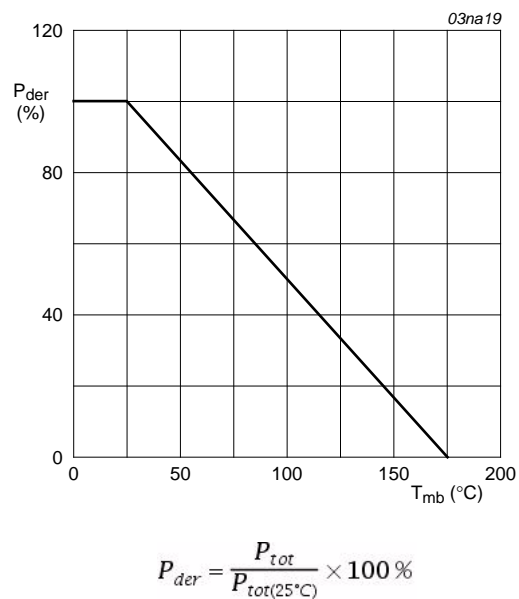
**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

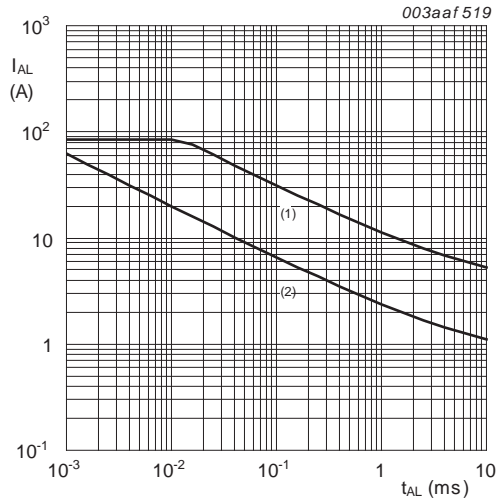
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	25	V
V <sub>DGR</sub>	drain-gate voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C; R <sub>GS</sub> = 20 kΩ	-	25	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; see <a href="#">Figure 1</a>	-	84	A
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; see <a href="#">Figure 1</a>	-	60	A
I <sub>DM</sub>	peak drain current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C; see <a href="#">Figure 4</a>	-	336	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <a href="#">Figure 2</a>	-	61	W
T <sub>stg</sub>	storage temperature		-55	175	°C
T <sub>j</sub>	junction temperature		-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature		-	260	°C
V <sub>ESD</sub>	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	200	-	V
<b>Source-drain diode</b>					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	55	A
I <sub>SM</sub>	peak source current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C	-	336	A
<b>Avalanche ruggedness</b>					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 84 A; V <sub>sup</sub> ≤ 25 V; R <sub>GS</sub> = 50 Ω; unclamped; see <a href="#">Figure 3</a>	-	17.4	mJ



**Fig 1. Continuous drain current as function of mounting base temperature**



**Fig 2. Normalized total power dissipation as a function of mounting base temperature**



(1)  $T_{j(imit)} = 25^{\circ}C$ ; (2)  $T_{j(imit)} = 100^{\circ}C$

Fig 3. Single pulse avalanche rating; avalanche current as a function of avalanche time

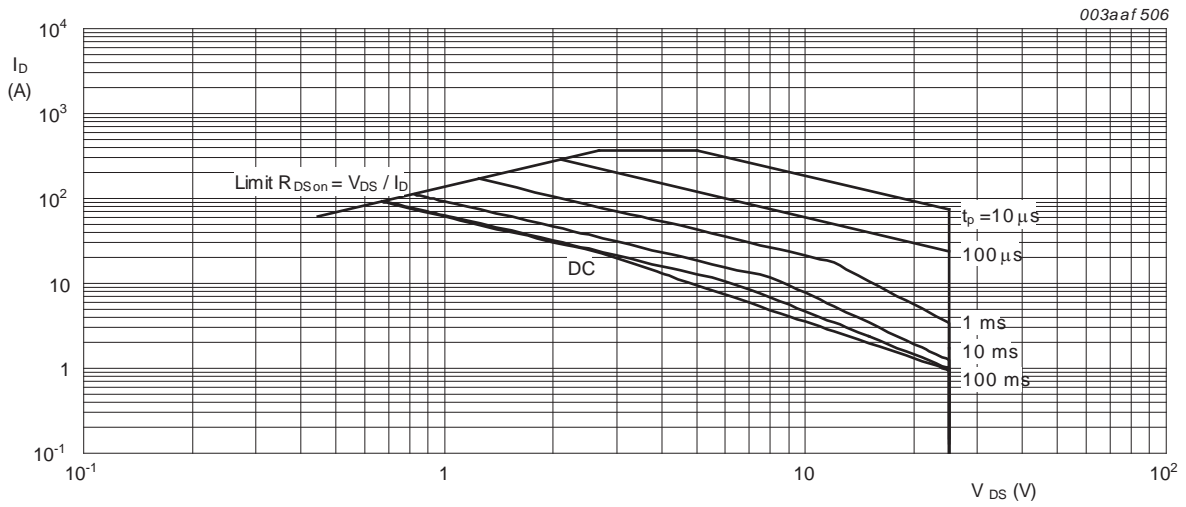


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <a href="#">Figure 5</a>	-	1.4	2.4	K/W

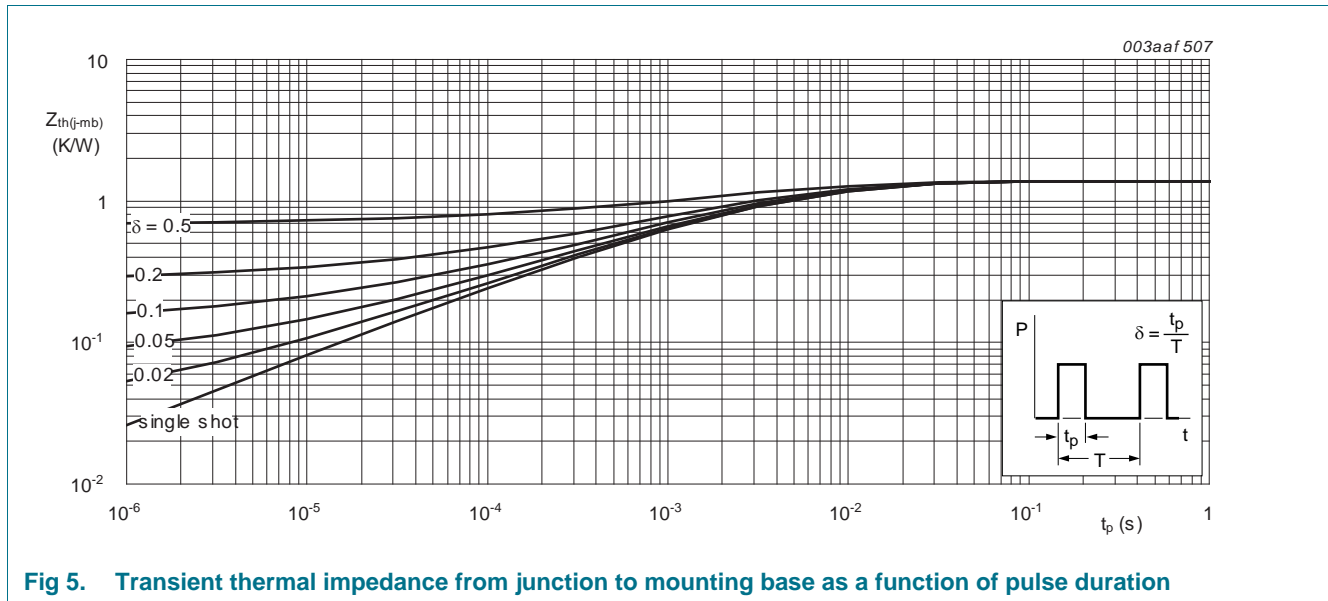


Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 6. Characteristics

**Table 6. Characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	25	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	22.5	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$ ; see <a href="#">Figure 10</a>	1.05	1.53	1.95	V
		$I_D = 10 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ }^\circ C$ ; see <a href="#">Figure 11</a>	0.5	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ C$ ; see <a href="#">Figure 11</a>	-	-	2.25	V
$I_{DSS}$	drain leakage current	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	-	1	$\mu A$
		$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ }^\circ C$	-	-	100	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	-	100	nA
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	-	100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 20 \text{ A}; T_j = 25 \text{ }^\circ C$ ; see <a href="#">Figure 12</a>	-	4.5	5.8	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 20 \text{ A}; T_j = 150 \text{ }^\circ C$ ; see <a href="#">Figure 12</a> ; see <a href="#">Figure 13</a>	-	-	9.85	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A}; T_j = 25 \text{ }^\circ C$ ; see <a href="#">Figure 12</a>	-	3.5	4.5	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 20 \text{ A}; T_j = 150 \text{ }^\circ C$ ; see <a href="#">Figure 12</a> ; see <a href="#">Figure 13</a>	-	-	7.65	mΩ
$R_G$	internal gate resistance (AC)	$f = 1 \text{ MHz}$	-	2.1	4.2	Ω
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 20 \text{ A}; V_{DS} = 12 \text{ V}; V_{GS} = 10 \text{ V}$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	22.8	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$ ; see <a href="#">Figure 14</a>	-	21.1	-	nC
		$I_D = 20 \text{ A}; V_{DS} = 12 \text{ V}; V_{GS} = 4.5 \text{ V}$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	10.9	-	nC
$Q_{GS}$	gate-source charge		-	3.3	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	2.25	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	1.05	-	nC
$Q_{GD}$	gate-drain charge	$I_D = 20 \text{ A}; V_{DS} = 12 \text{ V}; V_{GS} = 4.5 \text{ V}$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	3.5	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$V_{DS} = 12 \text{ V}$ ; see <a href="#">Figure 14</a> ; see <a href="#">Figure 15</a>	-	2.58	-	V
$C_{iss}$	input capacitance	$V_{DS} = 12 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ C$ ; see <a href="#">Figure 16</a>	-	1407	-	pF
$C_{oss}$	output capacitance		-	354	-	pF
$C_{rss}$	reverse transfer capacitance		-	119	-	pF

Table 6. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{d(on)}$	turn-on delay time	$V_{DS} = 12\text{ V}; R_L = 0.5\ \Omega; V_{GS} = 4.5\text{ V};$ $R_{G(ext)} = 4.7\ \Omega$	-	15.9	-	ns
$t_r$	rise time		-	17.5	-	ns
$t_{d(off)}$	turn-off delay time		-	24	-	ns
$t_f$	fall time		-	9.9	-	ns
$Q_{oss}$	output charge	$V_{GS} = 0\text{ V}; V_{DS} = 12\text{ V}; f = 1\text{ MHz};$ $T_j = 25\text{ }^\circ\text{C}$	-	7.32	-	nC

Source-drain diode

$V_{SD}$	source-drain voltage	$I_S = 20\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C};$ see <a href="#">Figure 17</a>	-	0.8	1.1	V
$t_{rr}$	reverse recovery time	$I_S = 20\text{ A}; di_S/dt = -100\text{ A}/\mu\text{s}; V_{GS} = 0\text{ V};$ $V_{DS} = 12\text{ V}$	-	24.5	-	ns
$Q_r$	recovered charge		-	16.1	-	nC
$t_a$	reverse recovery rise time	$V_{GS} = 0\text{ V}; I_S = 20\text{ A}; di_S/dt = -100\text{ A}/\mu\text{s};$ $V_{DS} = 12\text{ V};$ see <a href="#">Figure 18</a>	-	14.9	-	ns
$t_b$	reverse recovery fall time		-	9.6	-	ns

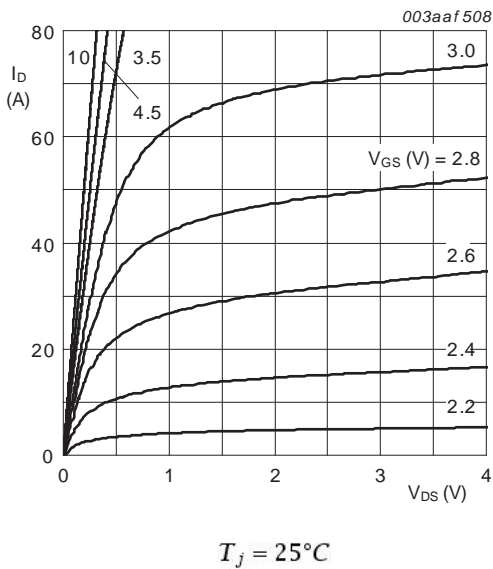


Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values

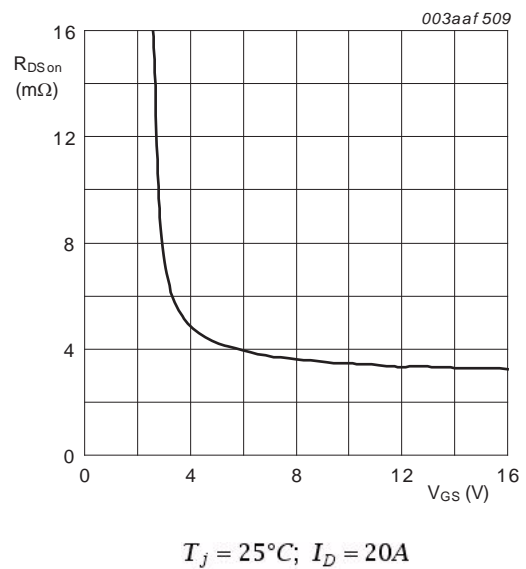
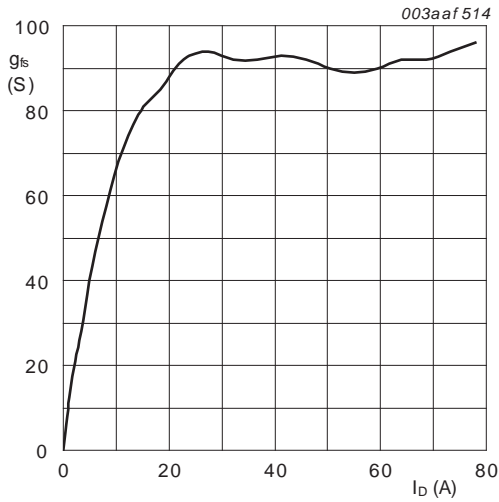
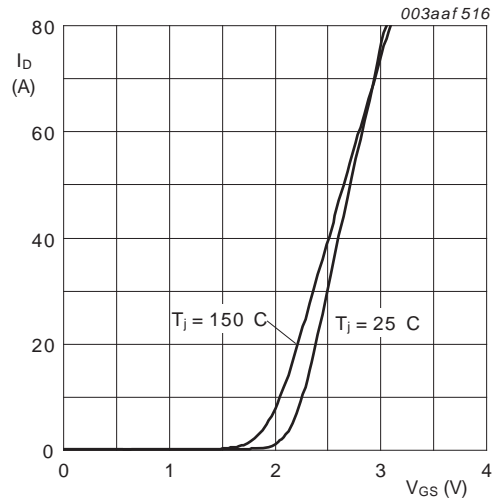


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values



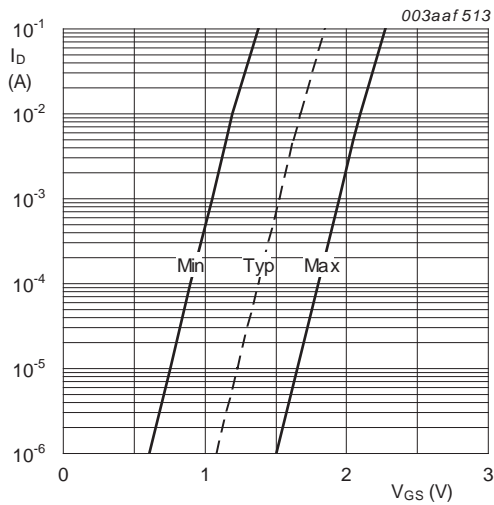
$T_j = 25^\circ\text{C}; V_{DS} = 10\text{V}$

Fig 8. Forward transconductance as a function of drain current; typical values



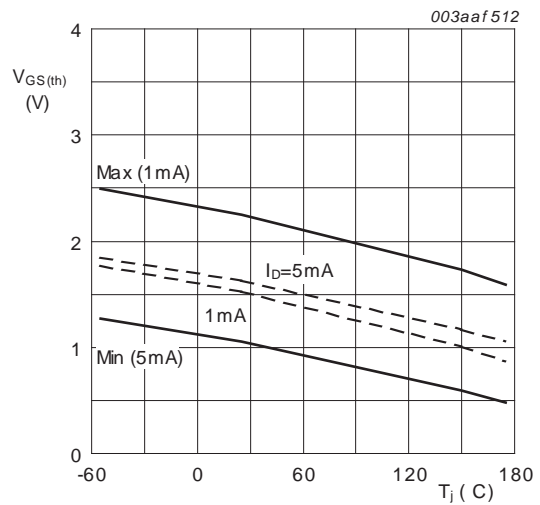
$V_{DS} = 10\text{V}$

Fig 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values



$T_j = 25^\circ\text{C}; V_{DS} = 25\text{V}$

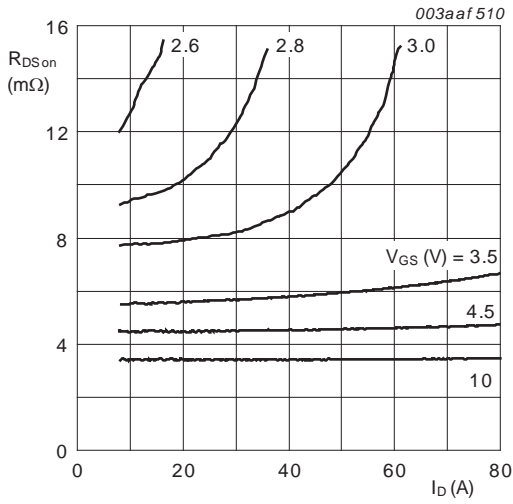
Fig 10. Sub-threshold drain current as a function of gate-source voltage



$V_{DS} = V_{GS}$

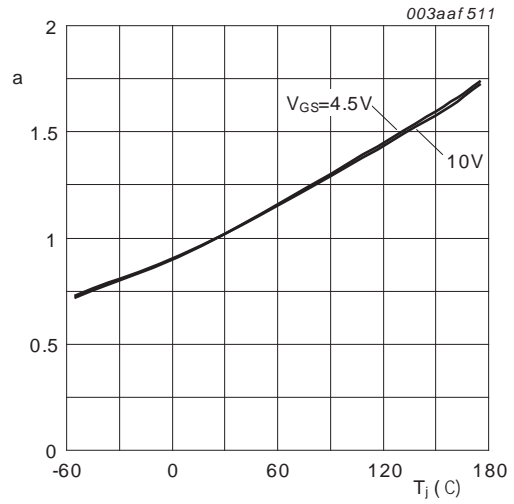
Fig 11. Gate-source threshold voltage as a function of junction temperature





$T_j = 25^\circ\text{C}$

Fig 12. Drain-source on-state resistance as a function of drain current; typical values



$$a = \frac{R_{DSon}}{R_{DSon}(25^\circ\text{C})}$$

Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

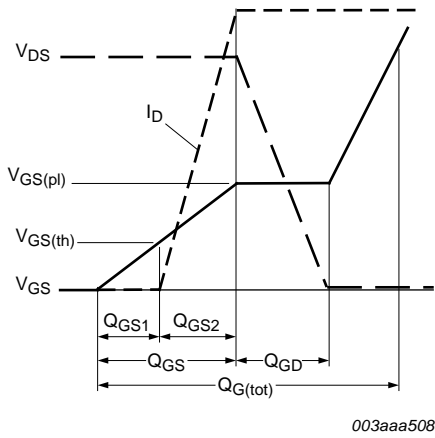
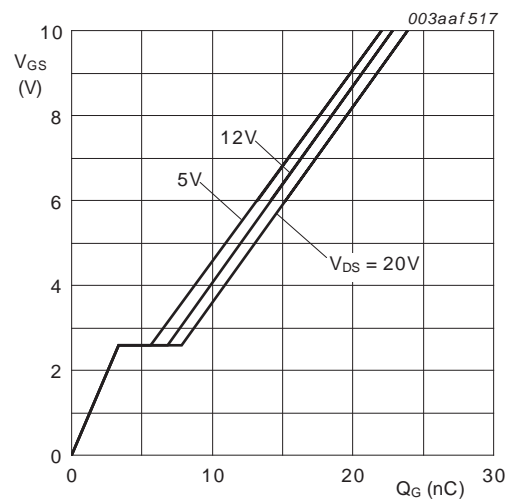
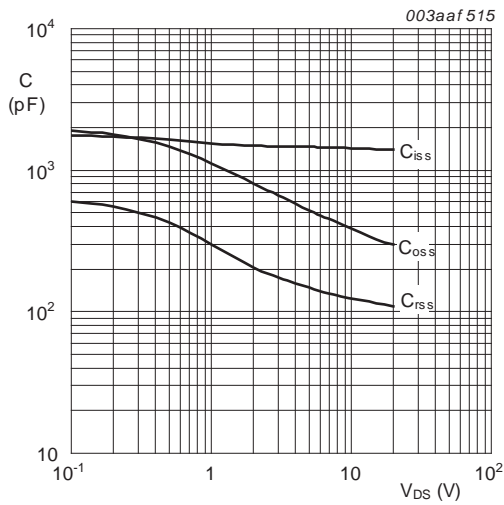


Fig 14. Gate charge waveform definitions



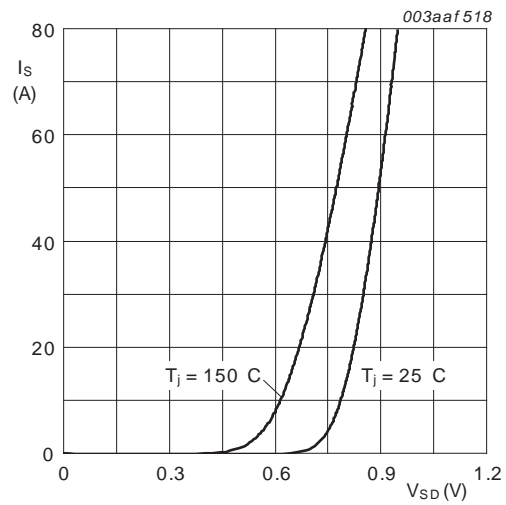
$T_j = 25^\circ\text{C}; I_D = 20\text{A}$

Fig 15. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0V; f = 1MHz$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$V_{GS} = 0V$

Fig 17. Source current as a function of source-drain voltage; typical values

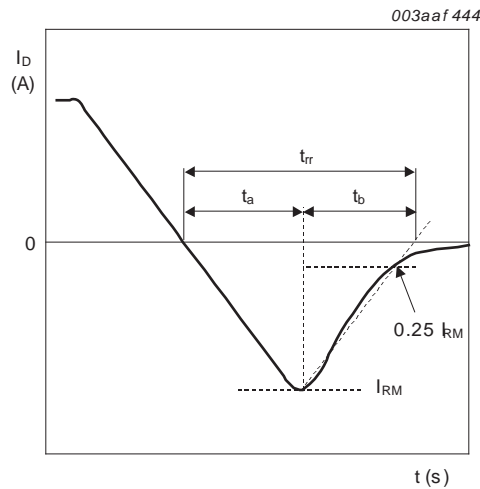


Fig 18. Reverse recovery timing definition

7. Package outline

Plastic single-ended surface-mounted package (LPAK); 4 leads

SOT669

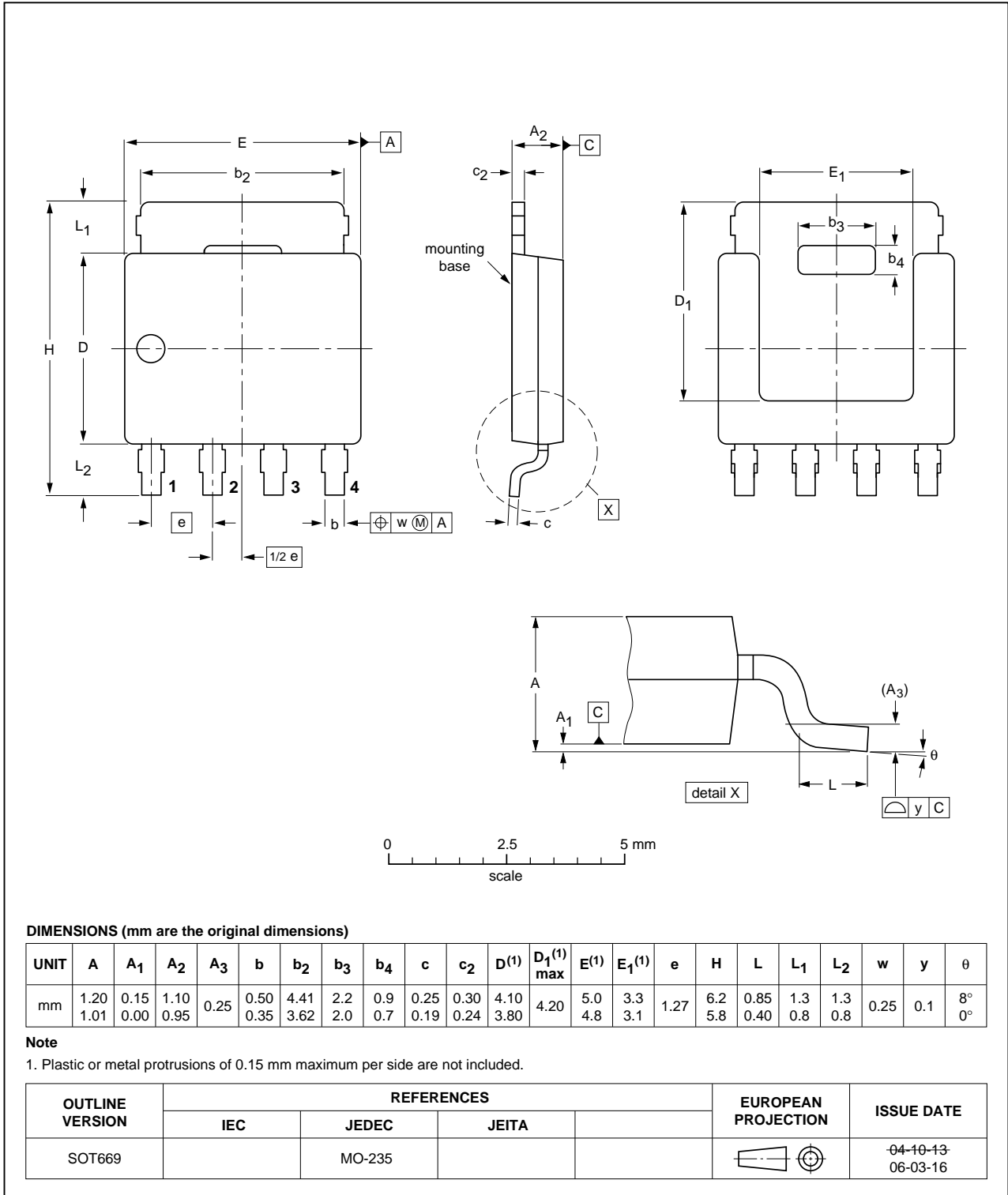


Fig 19. Package outline SOT669 (LPAK)

## 8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN4R0-25YLC v.1	20101202	Product data sheet	-	-

## 9. Legal information

### 9.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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## 11. Contents

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Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.